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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10045542	FILING DATE 10/25/2001	CLASS 427	SUBCLASS 377	GAU 1762	EXAMINER B...
APPLICANTS: Das Minal; Lipkin Lori;					
**CONTINUING DATA VERIFIED: is a CIP of 09/968,391 10/1/2001 which THIS APPLN CLAIMS BENEFIT OF 60/294,307 05/30/2001 AND IS A CIP OF 09/934,283 04/12/2001 WHICH CLAIMS BENEFIT OF 60/237,822 10/03/2000 AND CLAIMS BENEFIT OF 60/237,426 10/03/2000					
** FOREIGN APPLICATIONS VERIFIED: none 7					
PG-PUB TO NOT PUBLISH <input type="checkbox"/>			RESCIND <input type="checkbox"/>		
Foreign priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no			ATTORNEY DOCKET NO 5308-1571P2		
Verified and Acknowledged Examiners's Initials					
TITLE: Method of fabricating an oxide layer on a silicon carbide layer utilizing an anneal in a hydrogen environment					

U.S. DEPT. OF COMM/PAT. & TM-PTO-436 (Rev. 12-94)

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NOTICE OF ALLOWANCE MAILED 6-27-03		CLAIMS ALLOWED Total Claims 20 Print Claim for O.G. 1	
ISSUE FEE Amount Due \$1600 Date Paid		DRAWING Sheets Drwg. 6 Figs. Drwg. 8 Print Fig. 14	
TERMINAL DISCLAIMER		Application Examiner	
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